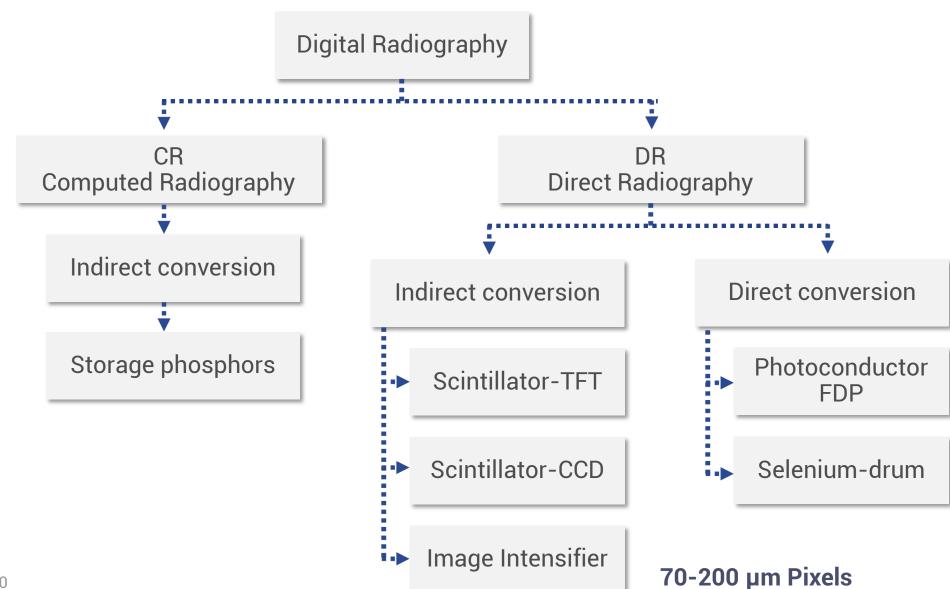
# Micron Scale Pixel Hybrid Detector for Hard X-rays

Christopher C. Scott, PhD<sup>1</sup>
Karim S. Karim, PhD, PEng, MBA<sup>1,2</sup>



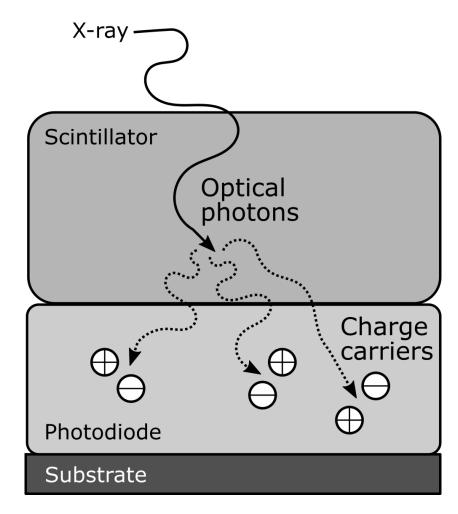
# **Digital Radiography**



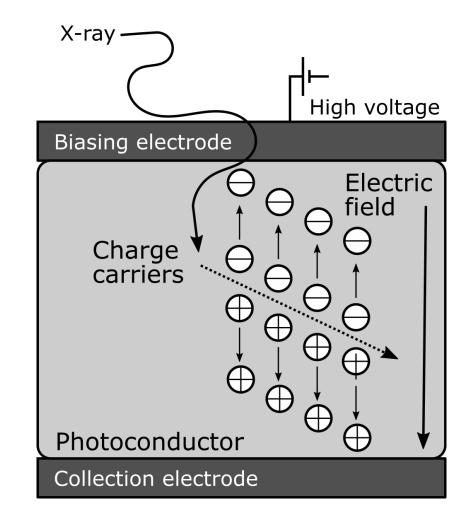




#### **Solid-State X-ray Detection**



**Indirect conversion** 

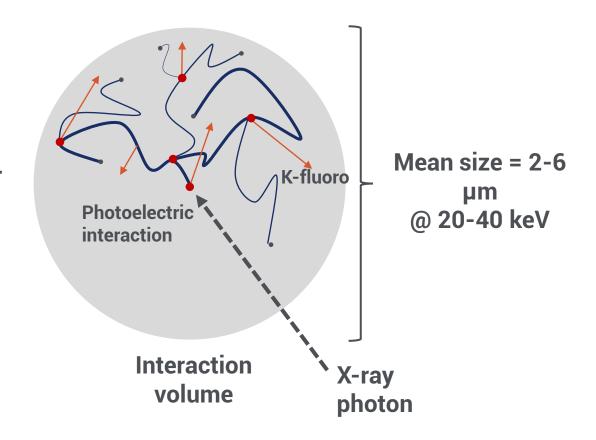


**Direct conversion** 



#### **Amorphous Selenium (a-Se) Photoconductor**

- Easily processed as a uniform thick layer over large area
- Atomic number (34) sufficient for hard x-ray imaging
- Low dark current & High charge collection efficiency

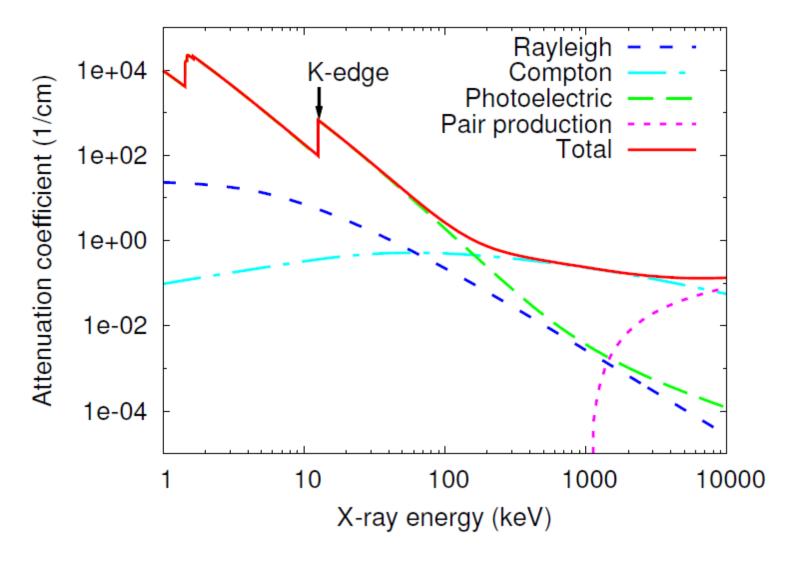


High Inherent Spatial Resolution, High Absorption for **Diagnostic X-rays** 

→ Low noise, Small Pixel Pitch CMOS

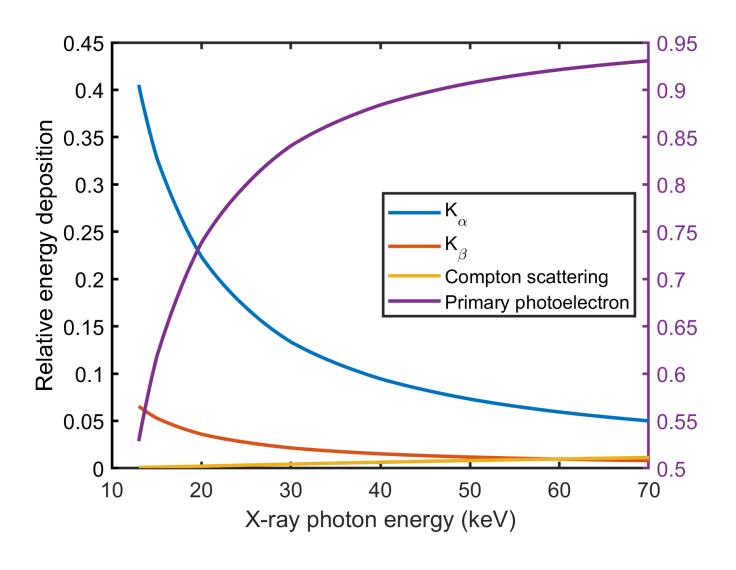


#### X-ray Attenuation Coefficients for a-Se





#### X-ray Interaction Energy Deposition in a-Se



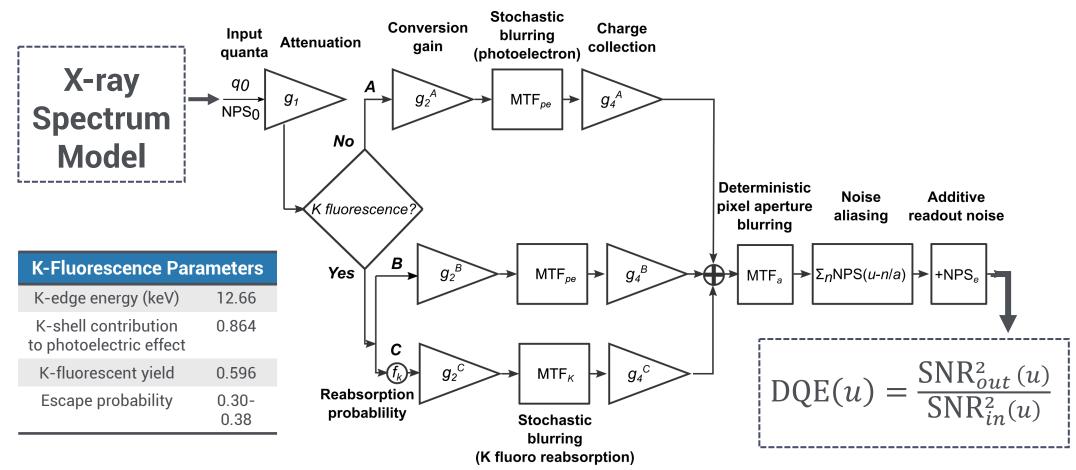
#### 35 keV

$$p_{pe} = 0.866$$
 $p_{K_{\alpha}} = 0.111$ 
 $p_{K_{\beta}} = 0.018$ 
 $p_{C} = 0.005$ 

**Weighting Factors** 



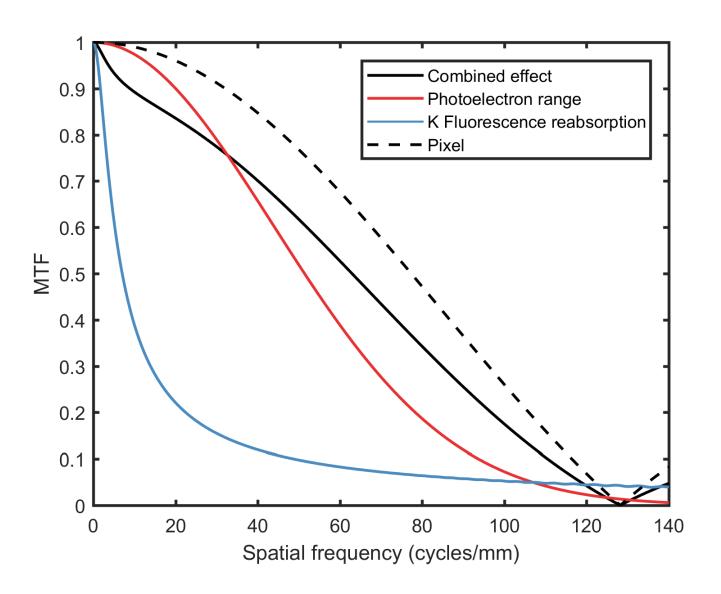
# **Cascaded Systems Theory**



**Detective Quantum Efficiency (DQE)** 



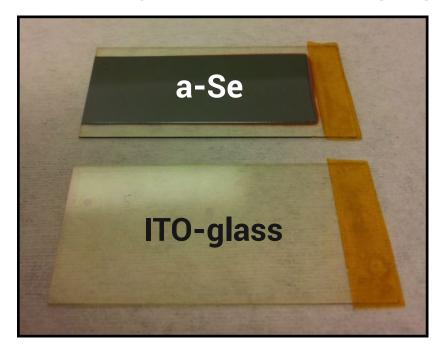
### X-ray Interaction MTF for a-Se



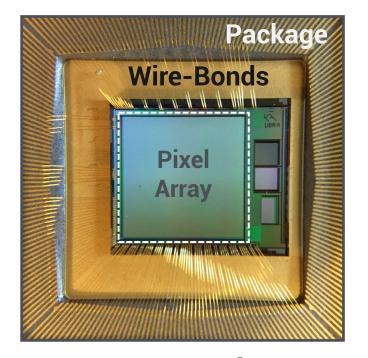


# Objective

Develop hybrid a-Se/CMOS detectors to achieve a unique combination of high spatial resolution (≤10 µm pixel) and high quantum efficiency for hard x-rays for X-ray diffraction imaging



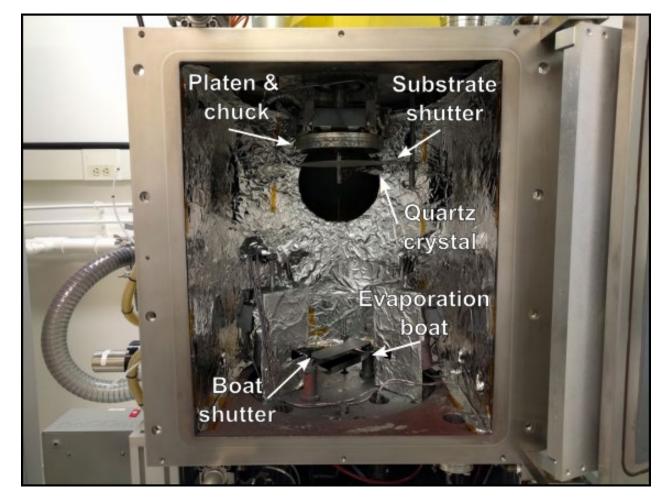
a-Se Films on ITO-glass by Physical Vapor Deposition



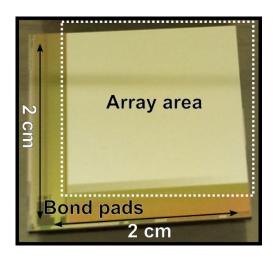
CMOS Readout Integrated Circuit (ROIC)



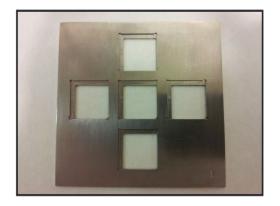
### Deposition of a-Se Films by Thermal Evaporation



Thermal Evaporator for a-Se at G2N Centre, University of Waterloo



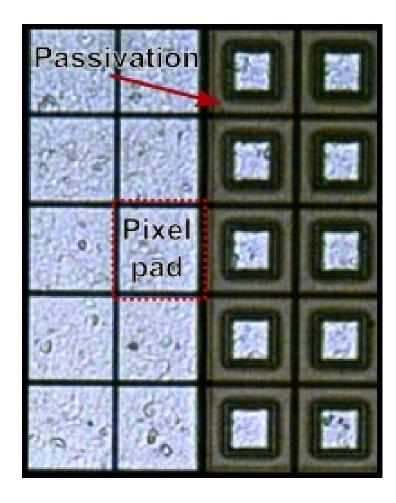
**CMOS Readout IC** 



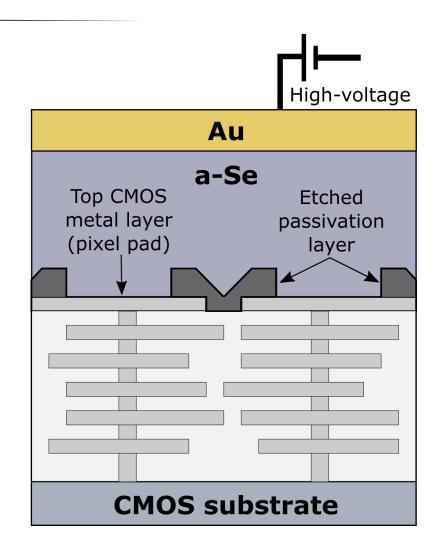
**Shadow Mask** 



#### **Back-end Processing of CMOS ROIC**



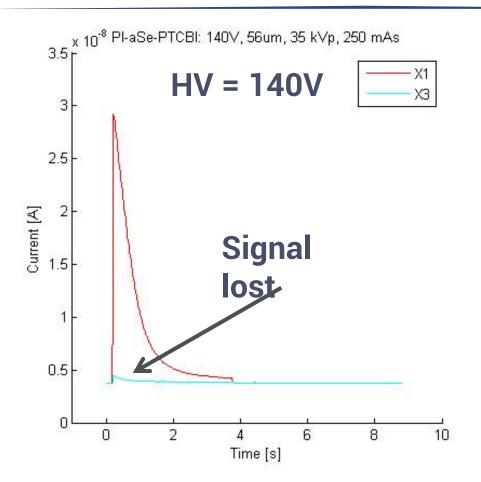
A micrograph of etched CMOS passivation

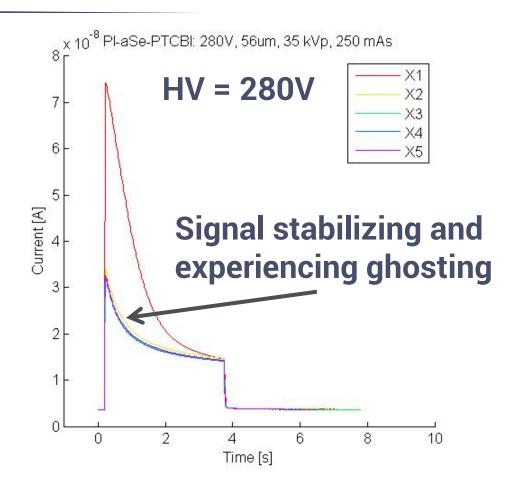


A diagram of the a-Se/CMOS detector cross-section



#### **Polyimide Layer Conduction**





35 kVp, 250 mAs 1 min. between exposures 5 min. between HV changes)

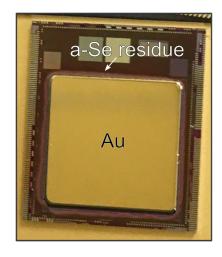
- Charge build-up at the a-Se/PI -> E-field reduction -> sensitivity loss
- Reversing the detector bias resets the device.

#### LIBRA Readout IC

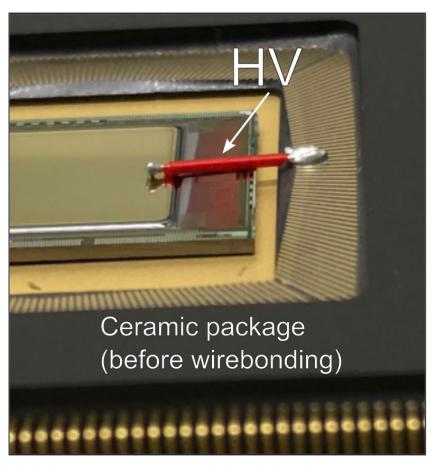
- 3T active pixel sensor
- $7.8 \times 7.8 \ \mu m^2$  pixel pitch
- 1000 × 1000 pixel array
- $7.8 \times 7.8 \text{ mm}^2$  imaging area



a-Se Deposition



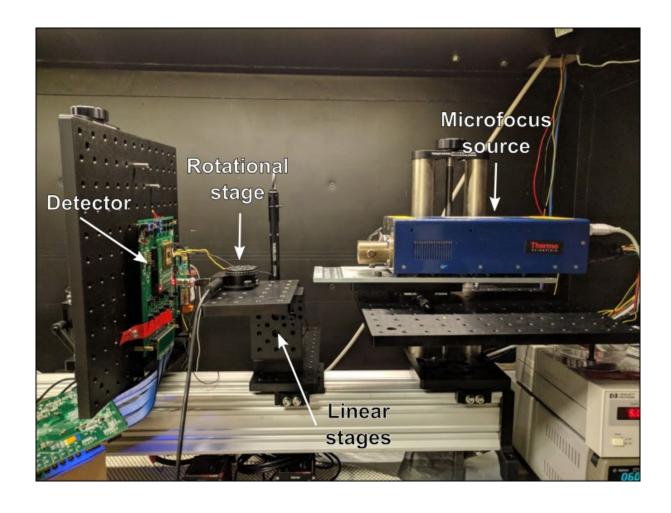
**Au Deposition** 



**Packaging** 

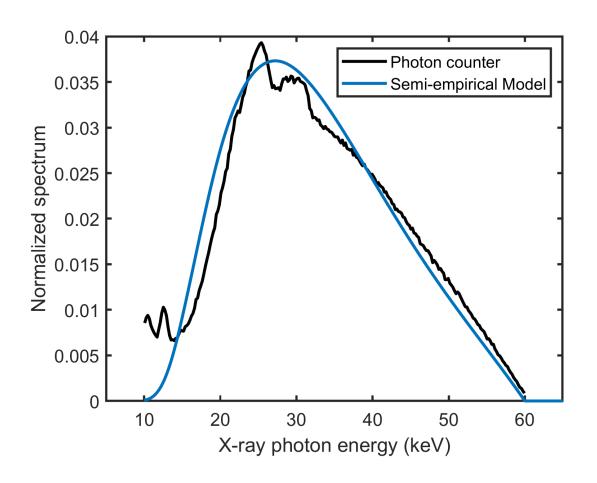


# LIBRA @ University of Waterloo





#### Microfocus Spectrum Characterization

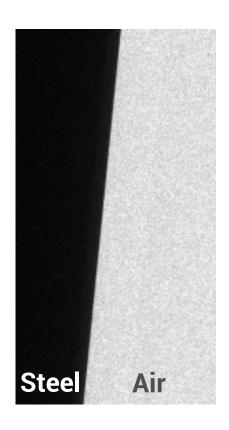


Tube potential (kV)	60
Filter (mm Al)	3.0
Half-value-layer (mm Al)	1.69
Mean Energy (keV)	34.3
Fluence per Exposure (mm <sup>-2</sup> R <sup>-1</sup> )	1.26 × 10 <sup>8</sup>

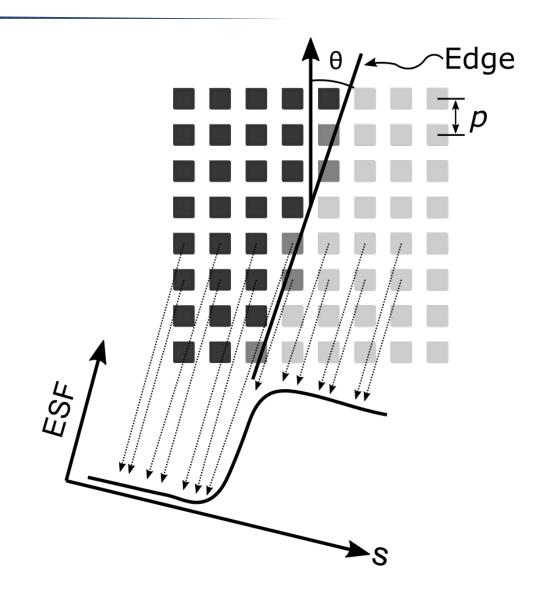
9 µm spot size



# Slanted-Edge Technique

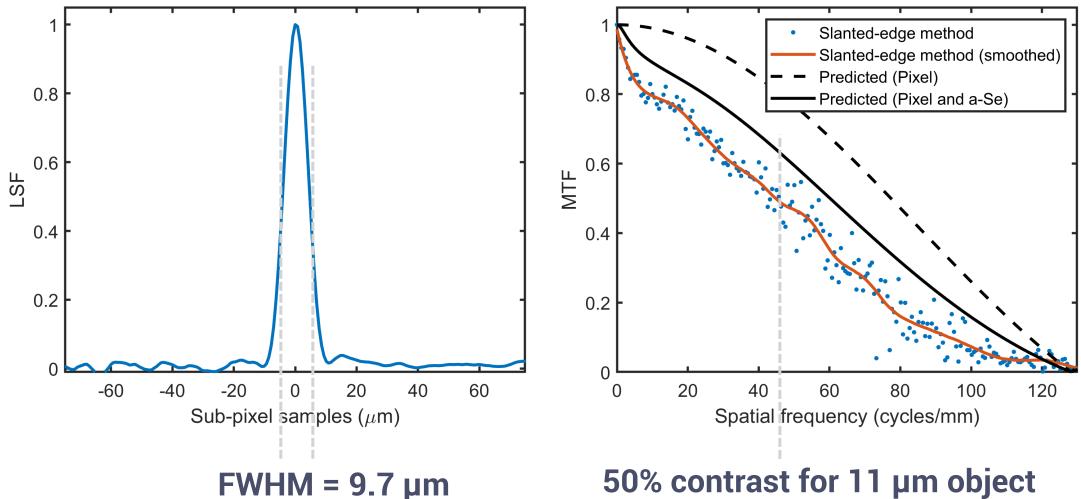


**Edge image** 





#### **LIBRA Spatial Resolution**



50% contrast for 11 µm object

High Resolution Scintillator Comparison: 15 μm GADOX 9 μm pixel FWHM = 27 μm Larsson et al., Scientific Reports 6, 2016

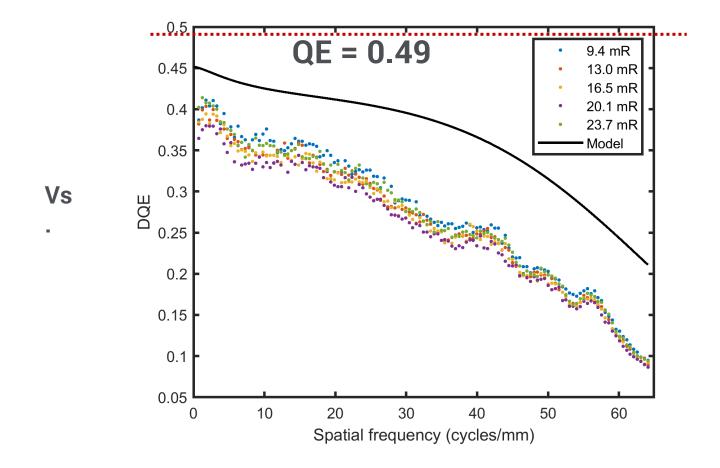


#### LIBRA DQE

#### **Best reported to date:**

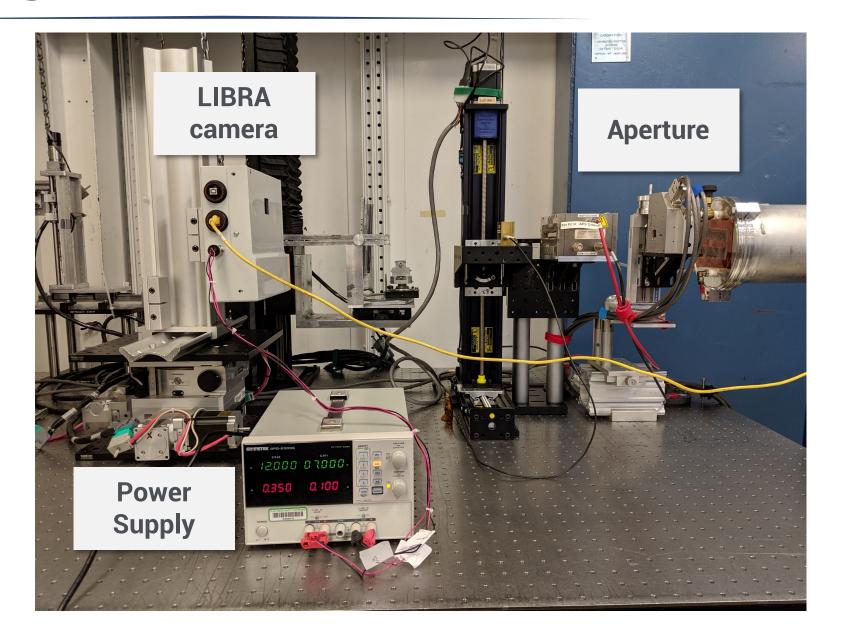
15 μm GADOX 9 μm pixel QE = 0.13

Larsson et al., Scientific Reports 6, 2016



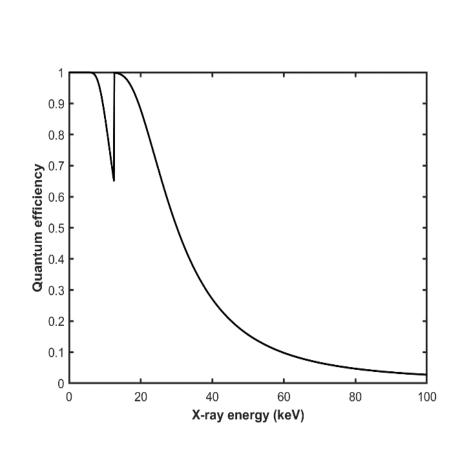


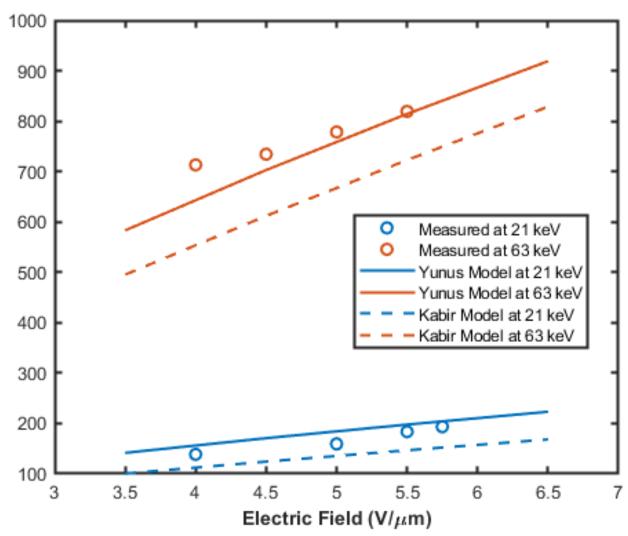
#### LIBRA @ ANL APS Beamline 1-BM





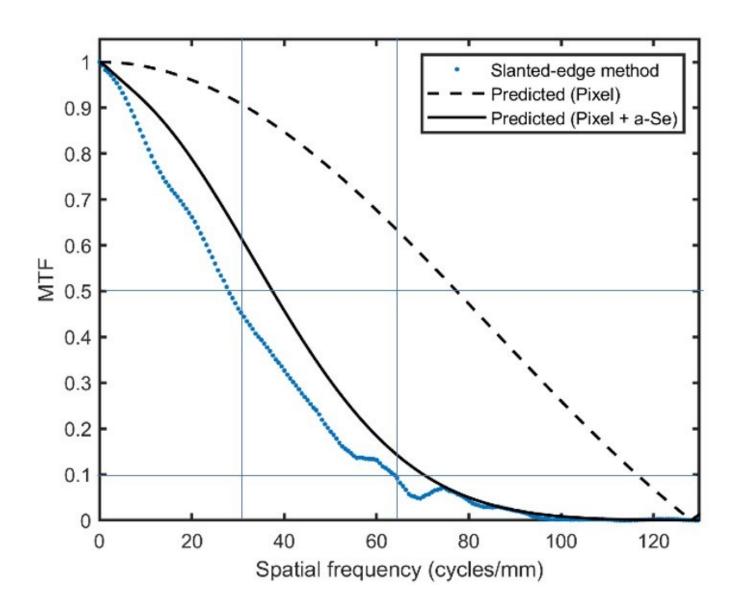
#### LIBRA Responsivity @ 21 keV and 63 keV







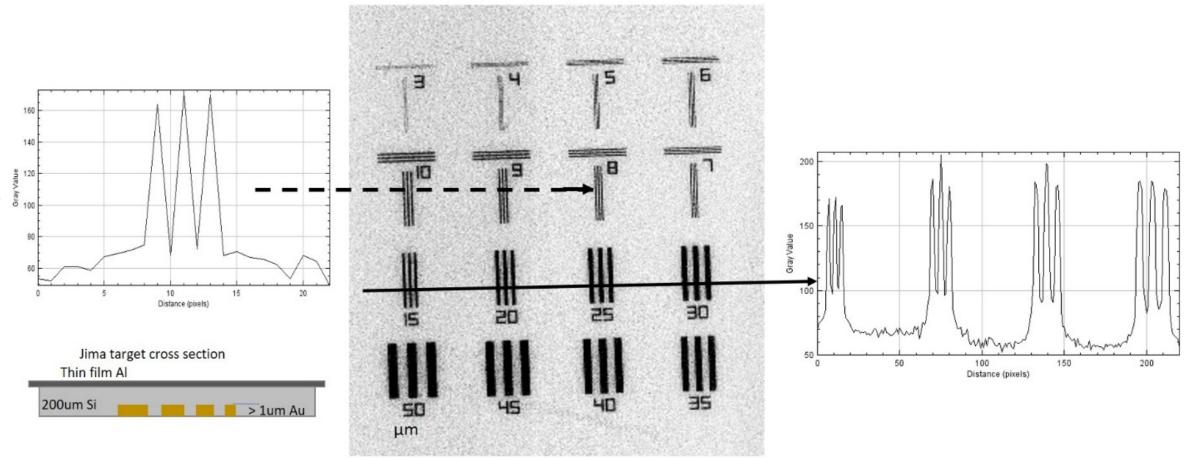
#### LIBRA Spatial Resolution @ 63 keV





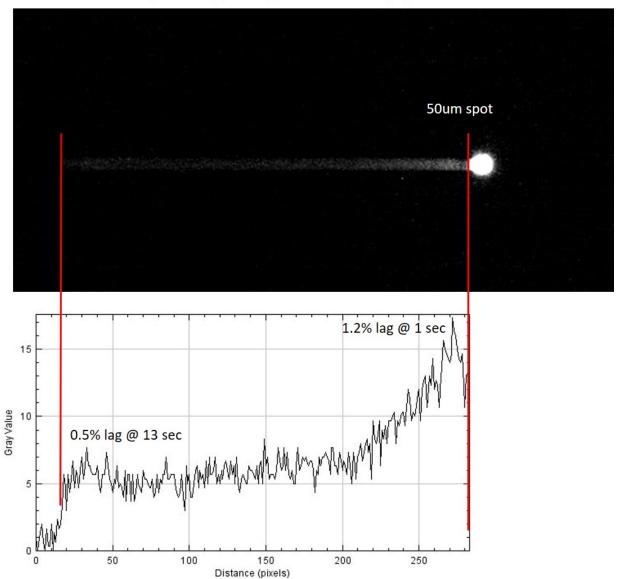
#### JIMA RT RC-05 Transmission Bar Target @ 21 keV

JIMA RT RC-05 Image \_21keV\_100fr avg\_250ms Tint



### 50 µm Pinhole Lag @ 63 keV

Scanning Pin Hole \_ 63 KeV\_ Scan Rate = 25.6 pix/sec



#### Conclusions

 The a-Se/CMOS prototypes demonstrate a remarkable combination of high spatial resolution and high quantum efficiency for hard x-rays

Factor of 3x DQE improvement despite being relatively unoptimized



#### Acknowledgements

#### **Michael Farrier**

Farrier Microengineering LLC, 3798 N M-75, Boyne City, Michigan, 49712, USA

#### **Antonino Miceli and Peter Kenesei**

X-ray Science Division Advanced Photon Source, Argonne National Laboratory, 9700 S. Cass Avenue, Lemont, IL, 60439, United States



#### Thank you



